Andr Vantomme

List of Publications by Year in Descending Order

410 papers	6,917 citations	40 h-index	63 g-index
427 ext. papers	7,459 ext. citations	3.2 avg, IF	5.34 L-index

#	Paper	IF	Citations
410	Ensemble RBS: probing the compositional profile of 3D microscale structures. *Surfaces and Interfaces*, **2022**, 102101	4.1	0
409	Ion beam modification of the Ni-Si solid-phase reaction: The influence of substrate damage and nitrogen impurities introduced by ion implantation. *Journal Physics D: Applied Physics*, **2021**, 54, 015307	3	4
408	Acid-Base Mediated Ligand Exchange on Near-Infrared Absorbing, Indium-Based III-V Colloidal Quantum Dots. *Journal of the American Chemical Society*, **2021**, 143, 4290-4301	16.4	13
407	Lattice Location Studies of the Amphoteric Nature of Implanted Mg in GaN. *Advanced Electronic Materials*, **2021**, 7, 2100345	6.4	1
406	Tuning size and coverage of Pd nanoparticles using atomic layer deposition. *Applied Surface Science* , **2021**, 539, 148238	6.7	1
405	The influence of phonon softening on the superconducting critical temperature of Sn nanostructures. *Scientific Reports*, **2020**, 10, 5729	4.9	6
404	A generalized fitting tool for analysis of two-dimensional channeling patterns. *Nuclear Instruments & Methods in Physics Research B*, **2020**, 462, 102-113	1.2	5
403	Direct Structural Identification and Quantification of the Split-Vacancy Configuration for Implanted Sn in Diamond. *Physical Review Letters*, **2020**, 125, 045301	7.4	8
402	Lattice sites of implanted Na in GaN and AlN in comparison to other light alkalis and alkaline earths. *Journal of Applied Physics*, **2020**, 128, 045703	2.5	2
401	Impurity-enhanced solid-state amorphization: the Ni□Si thin film reaction altered by nitrogen. *Journal Physics D: Applied Physics*, **2019**, 52, 145301	3	5
400	Tailored Ag-Cu-Mg multielemental nanoparticles for wide-spectrum antibacterial coating. *Nanoscale*, **2019**, 11, 1626-1635	7.7	42
399	Magnetic characterization of oblique angle deposited Co/CoO on gold nanoparticles. *Journal of Magnetism and Magnetic Materials*, **2019**, 483, 76-82	2.8	3
398	In situ study of the □Sn to □Sn phase transition in low-dimensional systems: Phonon behavior and thermodynamic properties. *Physical Review B*, **2019**, 100,	3.3	8
397	Alternative approach to populate and study the Th229 nuclear clock isomer. *Physical Review C*, **2019**, 100,	2.7	8
396	Lithium Diffusion in Copper. *Journal of Physical Chemistry Letters*, **2019**, 10, 5206-5210	6.4	12
395	Experimental observation of electron-phonon coupling enhancement in Sn nanowires caused by phonon confinement effects. *Physical Review B*, **2019**, 99,	3.3	7
394	Controlling the formation and stability of ultra-thin nickel silicides - An alloying strategy for preventing agglomeration. *Journal of Applied Physics*, **2018**, 123, 075303	2.5	18

393	Oxide reduced silicon nanowires. *Current Applied Physics*, **2018**, 18, 576-582	2.6	4
392	Impact of magnetization and hyperfine field distribution on high magnetoelectric coupling strength in BaTiO-BiFeO multilayers. *Nanoscale*, **2018**, 10, 5574-5580	7.7	12
391	Deposition and patterning of magnetic atom trap lattices in FePt films with periods down to 200 nm. *Journal of Applied Physics*, **2018**, 124, 044902	2.5	2
390	Morphology-induced spin frustration in granular BiFeO3 thin films: Origin of the magnetic vertical shift. *Applied Physics Letters*, **2018**, 113, 142402	3.4	2
389	The Surface Chemistry of Colloidal HgSe Nanocrystals, toward Stoichiometric Quantum Dots by Design. *Chemistry of Materials*, **2018**, 30, 7637-7647	9.6	13
388	Lateral Magnetically Modulated Multilayers by Combining Ion Implantation and Lithography. *Small*, **2017**, 13, 1603465	11	9
387	Lattice Location of Mg in GaN: A Fresh Look at Doping Limitations. *Physical Review Letters*, **2017**, 118, 095501	7.4	29
386	The role of composition and microstructure in Ni□V silicide formation and low temperature epitaxial NiSi2 growth by premixing Si. *Journal Physics D: Applied Physics*, **2017**, 50, 065303	3	2
385	Interface induced out-of-plane magnetic anisotropy in magnetoelectric BiFeO3-BaTiO3 superlattices. *Applied Physics Letters*, **2017**, 110, 092902	3.4	12
384	Multipurpose setup for low-temperature conversion electron M□sbauer spectroscopy. *Review of Scientific Instruments*, **2017**, 88, 053901	1.7	3
383	Calibration of PIXE yields using Cu as a reference. *Nuclear Instruments & Methods in Physics Research B*, **2017**, 406, 115-118	1.2	1
382	Ternary silicide formation from Ni-Pt, Ni-Pd and Pt-Pd alloys on Si(100): Nucleation and solid solubility of the monosilicides. *Acta Materialia*, **2017**, 130, 19-27	8.4	8
381	Independent tuning of size and coverage of supported Pt nanoparticles using atomic layer deposition. *Nature Communications*, **2017**, 8, 1074	17.4	72
380	Formation of ultrathin Ni germanides: solid-phase reaction, morphology and texture. *Journal Physics D: Applied Physics*, **2017**, 50, 455301	3	5
379	Lattice dynamics in Sn nanoislands and cluster-assembled films. *Physical Review B*, **2017**, 95,	3.3	5
378	Evidence of tetragonal distortion as the origin of the ferromagnetic ground state in □e nanoparticles. *Physical Review B*, **2017**, 96,	3.3	1
377	The Institute for Nuclear and Radiation Physics at the University of Leuven. *Nuclear Physics News*, **2017**, 27, 18-22	0.7	1
376	Induced ferromagnetism and magnetoelectric coupling in ion-beam synthesized BiFeO3□CoFe2O4nanocomposite thin films. *Journal Physics D: Applied Physics*, **2016**, 49, 325302	3	15

375	PbS/CdS Core/Shell Quantum Dots by Additive, Layer-by-Layer Shell Growth. *Chemistry of Materials*, **2016**, 28, 6953-6959	9.6	27
374	Electric Polarity-Dependent Modification of the Fe/BaTiO3 Interface. *Advanced Materials Interfaces*, **2016**, 3, 1500433	4.6	1
373	50 years of ion channeling in materials science. *Nuclear Instruments & Methods in Physics Research B*, **2016**, 371, 12-26	1.2	18
372	An Inner-/Outer-Sphere Stabilized Sn Active Site in Zeolite: Spectroscopic Evidence and Kinetic Consequences. *ACS Catalysis*, **2016**, 6, 31-46	13.1	67
371	Interplay between relaxation and Sn segregation during thermal annealing of GeSn strained layers. *Journal of Applied Physics*, **2016**, 120, 145303	2.5	13
370	Correlation of High Magnetoelectric Coupling with Oxygen Vacancy Superstructure in Epitaxial Multiferroic BaTiO BiFeO Composite Thin Films. *Materials*, **2016**, 9,	3.5	14
369	Epitaxial Coherence at Interfaces as Origin of High Magnetoelectric Coupling in Multiferroic BaTiO3 BiFeO3 Superlattices. *Advanced Materials Interfaces*, **2016**, 3, 1500822	4.6	25
368	Thermal stability and relaxation mechanisms in compressively strained Ge0.94Sn0.06 thin films grown by molecular beam epitaxy. *Journal of Applied Physics*, **2016**, 120, 085309	2.5	5
367	Phase formation and texture of thin nickel germanides on Ge(001) and Ge(111). *Journal of Applied Physics*, **2016**, 119, 135305	2.5	14
366	Multidimensional Purcell effect in an ytterbium-doped ring resonator. *Nature Photonics*, **2016**, 10, 385-388	39.9	21
365	Interplay between magnetocrystalline anisotropy and exchange bias in epitaxial CoO/Co films. *Journal of Physics Condensed Matter*, **2016**, 28, 196002	1.8	9
364	A Case Study of ALD Encapsulation of Quantum Dots: Embedding Supported CdSe/CdS/ZnS Quantum Dots in a ZnO Matrix. *Journal of Physical Chemistry C*, **2016**, 120, 18039-18045	3.8	25
363	Cooperative Catalysis for Multistep Biomass Conversion with Sn/Al Beta Zeolite. *ACS Catalysis*, **2015**, 5, 928-940	13.1	137
362	Magnetic spin structure and magnetoelectric coupling in BiFeO3-BaTiO3 multilayer. *Applied Physics Letters*, **2015**, 106, 082904	3.4	22
361	Annealing effect on the optical properties and interdiffusion of MgO/Zr/MgO multilayered selective solar absorber coatings. *Solar Energy*, **2015**, 120, 123-130	6.8	24
360	Coexistence of superconductivity and ferromagnetism in cluster-assembled Sn Co nanocomposites. *Journal of Alloys and Compounds*, **2015**, 637, 509-516	5.7	6
359	Tailoring the magnetic anisotropy, magnetization reversal, and anisotropic magnetoresistance of Ni films by ion sputtering. *Physical Review B*, **2015**, 91,	3.3	14
358	Extended X-ray absorption fine structure investigation of Sn local environment in strained and relaxed epitaxial Ge1 Snx films. *Journal of Applied Physics*, **2015**, 117, 095702	2.5	20

357	Identification of the interstitial Mn site in ferromagnetic (Ga,Mn)As. *Applied Physics Letters*, **2015**, 106, 012406	3.4	5
356	Ion-induced pattern formation on indium tin oxide for alignment of liquid crystals. *Thin Solid Films*, **2015**, 589, 315-321	2.2	1
355	Ultrathin GeSn p-channel MOSFETs grown directly on Si(111) substrate using solid phase epitaxy. *Japanese Journal of Applied Physics*, **2015**, 54, 04DA07	1.4	6
354	Dynamical properties of ordered Fe□t alloys. *Journal of Alloys and Compounds*, **2015**, 651, 528-536	5.7	14
353	Correlation of magnetoelectric coupling in multiferroic BaTiO3-BiFeO3 superlattices with oxygen vacancies and antiphase octahedral rotations. *Applied Physics Letters*, **2015**, 106, 012905	3.4	49
352	Dislocation density and tetragonal distortion of a GaN epilayer on Si (111): A comparative RBS/C and TEM study. *Nuclear Instruments & Methods in Physics Research B*, **2014**, 331, 69-73	1.2	1
351	Multiferroic BaTiO3□BiFeO3composite thin films and multilayers: strain engineering and magnetoelectric coupling. *Journal Physics D: Applied Physics*, **2014**, 47, 135303	3	83
350	Calibration of PIXE yields using binary thin films on Si. *Nuclear Instruments & Methods in Physics Research B*, **2014**, 331, 65-68	1.2	2
349	Rotatable anisotropy driven training effects in exchange biased Co/CoO films. *Journal of Applied Physics*, **2014**, 115, 243903	2.5	18
348	Less is more. Cation exchange and the chemistry of the nanocrystal surface. *ACS Nano*, **2014**, 8, 7948-57	16.7	52
347	Relaxor ferroelectricity and magnetoelectric coupling in ZnO-Co nanocomposite thin films: beyond multiferroic composites. *ACS Applied Materials & Interfaces*, **2014**, 6, 4737-42	9.5	29
346	Surface Chemistry of CuInS2 Colloidal Nanocrystals, Tight Binding of L-Type Ligands. *Chemistry of Materials*, **2014**, 26, 5950-5957	9.6	53
345	Influence of the irradiation temperature on the surface structure and physical/chemical properties of Ar ion-irradiated bulk metallic glasses. *Journal of Alloys and Compounds*, **2014**, 610, 118-125	5.7	12
344	Phase formation in intermixed Ni□Ge thin films: Influence of Ge content and low-temperature nucleation of hexagonal nickel germanides. *Microelectronic Engineering*, **2014**, 120, 168-173	2.5	10
343	Emission channeling studies on transition-metal doped GaN and ZnO: Cation versus anion substitution. *Nuclear Instruments & Methods in Physics Research B*, **2014**, 332, 143-147	1.2	3
342	Electric Field-Induced Oxidation of Ferromagnetic/Ferroelectric Interfaces. *Advanced Functional Materials*, **2014**, 24, 71-76	15.6	24
341	Sequential multiple-step europium ion implantation and annealing of GaN. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2014**, 11, 253-257		9
340	The superconducting proximity effect in epitaxial Al/Pb nanocomposites. *Superconductor Science and Technology*, **2014**, 27, 015008	3.1	1

339	Structural and Optical Properties of Amorphous and Crystalline GeSn Layers on Si. *ECS Journal of Solid State Science and Technology*, **2014**, 3, P403-P408	2	14
338	Manipulating the asymmetry of magnetization reversal in epitaxial CoO/Co films. *Physical Review B*, **2014**, 90,	3.3	4
337	Interdependence between training and magnetization reversal in granular Co-CoO exchange bias systems. *Physical Review B*, **2014**, 89,	3.3	17
336	Tuning the ferromagnetic-antiferromagnetic interfaces of granular Co-CoO exchange bias systems by annealing. *Journal of Applied Physics*, **2014**, 115, 133915	2.5	13
335	On the formation and structural properties of hexagonal rare earth (Y, Gd, Dy, Er and Yb) disilicide thin films. *Journal of Alloys and Compounds*, **2014**, 611, 149-156	5.7	7
334	Searching for room temperature ferromagnetism in transition metal implanted ZnO and GaN. *Journal of Applied Physics*, **2013**, 113, 023903	2.5	31
333	Anisotropic magnetism and spin-dependent transport in Co nanoparticle embedded ZnO thin films. *Journal of Applied Physics*, **2013**, 114, 033909	2.5	8
332	Mesoporous Oxide-Diluted Magnetic Semiconductors Prepared by Co Implantation in Nanocast 3D-Ordered In2O3 Materials. *Journal of Physical Chemistry C*, **2013**, 117, 17084-17091	3.8	14
331	Minority anion substitution by Ni in ZnO. *Applied Physics Letters*, **2013**, 103, 091905	3.4	3
330	Influence of crystal mosaicity on axial channeling effects and lattice site determination of impurities. *Applied Physics Letters*, **2013**, 103, 172108	3.4	6
329	Magnetic properties of single crystalline expanded austenite obtained by plasma nitriding of austenitic stainless steel single crystals. *ACS Applied Materials & Interfaces*, **2013**, 5, 10118-26	9.5	11
328	Magnetic Anisotropy of Epitaxially Grown Fe/Mn/Co Trilayers. *IEEE Transactions on Magnetics*, **2013**, 49, 4525-4529	2	
327	Impact of ammonium sulfide solution on electronic properties and ambient stability of germanium surfaces: towards Ge-based microelectronic devices. *Journal of Materials Chemistry C*, **2013**, 1, 4105	7.1	10
326	On the growth kinetics of Ni(Pt) silicide thin films. *Journal of Applied Physics*, **2013**, 113, 163504	2.5	14
325	Lift-off protocols for thin films for use in EXAFS experiments. *Journal of Synchrotron Radiation*, **2013**, 20, 426-32	2.4	12
324	Surface Chemistry of CdTe Quantum Dots Synthesized in Mixtures of Phosphonic Acids and Amines: Formation of a Mixed Ligand Shell. *Journal of Physical Chemistry C*, **2013**, 117, 13936-13943	3.8	23
323	Improving the magnetic properties of Co-CoO systems by designed oxygen implantation profiles. *ACS Applied Materials & Interfaces*, **2013**, 5, 4320-7	9.5	20
322	Liquid-Phase Adsorption of Sulfur on Germanium: Reaction Mechanism and Atomic Geometry. *Journal of Physical Chemistry C*, **2013**, 117, 7451-7458	3.8	5

321	Paramagnetism and antiferromagnetic interactions in single-phase Fe-implanted ZnO. *Journal of Physics Condensed Matter*, **2013**, 25, 416001	1.8	12
320	RBS and PIXE analysis of chlorine contamination in ALD-Grown TiN films on silicon **2013**,		5
319	Ion-induced roughening and ripple formation on polycrystalline metallic films. *New Journal of Physics*, **2013**, 15, 093047	2.9	19
318	Precise lattice location of substitutional and interstitial Mg in AlN. *Applied Physics Letters*, **2013**, 103, 262102	3.4	9
317	Crystalline Properties and Strain Relaxation Mechanism of CVD Grown GeSn. *ECS Transactions*, **2013** , 50, 875-883	1	8
316	Crystalline Properties and Strain Relaxation Mechanism of CVD Grown GeSn. *ECS Journal of Solid State Science and Technology*, **2013**, 2, P134-P137	2	74
315	Single Crystalline GeSn on Silicon by Solid Phase Crystallization. *ECS Transactions*, **2013**, 50, 915-920	1	4
314	Oxidation and Sulfidation of Germanium Surfaces: A Comparative Atomic Level Study of Different Passivation Schemes. *ECS Transactions*, **2013**, 50, 569-579	1	2
313	Interplay between lattice dynamics and superconductivity in Nb3Sn thin films. *Physical Review B*, **2013**, 88,	3.3	5
312	The magnetic structure of exchange coupled FePt/FePt3 thin films. *Journal of Applied Physics*, **2013**, 113, 013909	2.5	8
311	Effect of high temperature deposition on CoSi2 phase formation. *Journal of Applied Physics*, **2013**, 113, 234902	2.5	0
310	On the nucleation of PdSi and NiSi2 during the ternary Ni(Pd)/Si(100) reaction. *Journal of Applied Physics*, **2013**, 114, 063518	2.5	4
309	Tensile strained GeSn on Si by solid phase epitaxy. *Applied Physics Letters*, **2013**, 102, 052106	3.4	52
308	Influence of magnetocrystalline anisotropy on the magnetization reversal mechanism in exchange bias Co/CoO bilayers. *Solid State Communications*, **2012**, 152, 292-295	1.6	8
307	Passivation of cobalt nanocluster assembled thin films with hydrogen. *Thin Solid Films*, **2012**, 520, 5584-5588	2.2	3
306	In situ study of the growth properties of Ni-rare earth silicides for interlayer and alloy systems on Si(100). *Journal of Applied Physics*, **2012**, 111, 043511	2.5	6
305	Tuning of the size and the lattice parameter of ion-beam synthesized Pb nanoparticles embedded in Si. *Journal Physics D: Applied Physics*, **2012**, 45, 035301	3	6
304	Determination of the dominant diffusing species during nickel and palladium germanide formation. *Thin Solid Films*, **2012**, 526, 261-268	2.2	14

303	Adsorption of O2 on Ge(100): Atomic Geometry and Site-Specific Electronic Structure. *Journal of Physical Chemistry C*, **2012**, 116, 9925-9929	3.8	13
302	Tuning quantum corrections and magnetoresistance in ZnO nanowires by ion implantation. *Nano Letters*, **2012**, 12, 666-72	11.5	38
301	Size-Dependent Optical Properties of Zinc Blende Cadmium Telluride Quantum Dots. *Journal of Physical Chemistry C*, **2012**, 116, 5049-5054	3.8	48
300	Exchange bias induced by O ion implantation in ferromagnetic thin films. *Journal Physics D: Applied Physics*, **2012**, 45, 405004	3	12
299	S-Passivation of the Ge Gate Stack Using (NH4)2S. *Solid State Phenomena*, **2012**, 187, 23-26	0.4	1
298	Stability and diffusion of interstitial and substitutional Mn in GaAs of different doping types. *Physical Review B*, **2012**, 86,	3.3	12
297	CVD Epitaxial Growth of GeSn Opens a New Route for Advanced Sn-Based Logic and Photonics Devices **2012**,		1
296	Direct observation of substitutional Ga after ion implantation in Ge by means of extended x-ray absorption fine structure. *Applied Physics Letters*, **2012**, 101, 261904	3.4	6
295	Evidence of N substitution by Mn in GaN. *Physical Review B*, **2012**, 86,	3.3	14
294	Anisotropic diffusion in FePt thin films. *Physical Review B*, **2012**, 85,	3.3	5
293	Lattice position and thermal stability of diluted As in Ge. *Journal of Applied Physics*, **2012**, 111, 053528	2.5	5
292	Practical limits for detection of ferromagnetism using highly sensitive magnetometry techniques. *Journal Physics D: Applied Physics*, **2011**, 44, 215001	3	33
291	Mixed Zn and O substitution of Co and Mn in ZnO. *Physical Review B*, **2011**, 84,	3.3	22
290	Paramagnetism and antiferromagnetic interactions in Cr-doped GaN. *Journal of Physics Condensed Matter*, **2011**, 23, 346004	1.8	6
289	Binding of Phosphonic Acids to CdSe Quantum Dots: A Solution NMR Study. *Journal of Physical Chemistry Letters*, **2011**, 2, 145-152	6.4	207
288	Fluence dependence of ion implantation-induced exchange bias in face centered cubic Co thin films. *Journal of Applied Physics*, **2011**, 110, 123902	2.5	10
287	Probing the magnetization inside a superconducting Nb film by nuclear resonant scattering. *Applied Physics Letters*, **2011**, 99, 092508	3.4	
286	Spacious and mechanically flexible mesoporous silica thin film composed of an open network of interlinked nanoslabs. *Journal of Materials Chemistry*, **2011**, 21, 7692		20

285	Characterization of GeSn materials for future Ge pMOSFETs source/drain stressors. *Microelectronic Engineering*, **2011**, 88, 342-346	2.5	89
284	Ge1−xSnx stressors for strained-Ge CMOS. *Solid-State Electronics*, **2011**, 60, 53-57	1.7	28
283	Formation of Ni(Ge1−xSnx) layers with solid-phase reaction in Ni/Ge1−xSnx/Ge systems. *Solid-State Electronics*, **2011**, 60, 46-52	1.7	22
282	Sn diffusion during Ni germanide growth on Ge1−xSnx. *Applied Physics Letters*, **2011**, 99, 211905	3.4	13
281	Simultaneous polarized neutron reflectometry and anisotropic magnetoresistance measurements. *Review of Scientific Instruments*, **2011**, 82, 033902	1.7	7
280	Direct identification of interstitial Mn in heavily p-type doped GaAs and evidence of its high thermal stability. *Applied Physics Letters*, **2011**, 98, 201905	3.4	23
279	Defect production in strained p-type Si1−xGex by Er implantation. *Journal of Applied Physics*, **2011**, 109, 013715	2.5	4
278	Electrical Characterization of Metastable Defects Introduced in GaN by Eu-Ion Implantation. *Materials Science Forum*, **2011**, 679-680, 804-807	0.4	4
277	Atomic Layer Deposition of High-□Dielectrics on Sulphur-Passivated Germanium. *Journal of the Electrochemical Society*, **2011**, 158, H687	3.9	18
276	Towards Passivation of Ge(100) Surfaces by Sulfur Adsorption from a (NH4)2S Solution: A Combined NEXAFS, STM and LEED Study. *Journal of the Electrochemical Society*, **2011**, 158, H589	3.9	10
275	Self-Affine Surface Roughness of Chemically and Thermally Cleaned Ge(100) Surfaces. *Journal of the Electrochemical Society*, **2011**, 158, H1090	3.9	4
274	(Invited) GeSn Technology: Impact of Sn on Ge CMOS Applications. *ECS Transactions*, **2011**, 41, 231-238	1	7
273	ALD on High Mobility Channels: Engineering the Proper Gate Stack Passivation. *ECS Transactions*, **2010**, 33, 9-23	1	4
272	Anisotropic lattice dynamics of FePt L10 thin films. *Physical Review B*, **2010**, 82,	3.3	11
271	Lattice location study of ion implanted Sn and Sn-related defects in Ge. *Physical Review B*, **2010**, 81,	3.3	23
270	Diluted manganese on the bond-centered site in germanium. *Applied Physics Letters*, **2010**, 97, 151914	3.4	17
269	Exchange bias by implantation of O ions into Co thin films. *Applied Physics Letters*, **2010**, 96, 132503	3.4	19
268	In situ x-ray diffraction study of Ni□b interlayer and alloy systems on Si(100). *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2010**, 28, 20-26	2.9	1

267	Spin structure in perpendicularly magnetized Fe-FePt bilayers. *Physical Review B*, **2010**, 82,	3.3	19
266	(Invited) Exploring the ALD Al2O3/In0.53Ga0.47As and Al2O3/Ge Interface Properties: A Common Gate Stack Approach for Advanced III-V/Ge CMOS. *ECS Transactions*, **2010**, 28, 173-183	1	10
265	(Invited) Assessment of Ge1-xSnx Alloys for Strained Ge CMOS Devices. *ECS Transactions*, **2010**, 33, 529-535	1	11
264	Direct observation of preferential heating near grain boundaries in patterned silicide films. *Journal of Applied Physics*, **2010**, 108, 063539	2.5	1
263	The influence of Pt redistribution on Ni1−xPtxSi growth properties. *Journal of Applied Physics*, **2010**, 108, 043505	2.5	23
262	Study of reorientation processes in L1-ordered FePt thin films. *Intermetallics*, **2010**, 18, 2069-2076	3.5	8
261	Identification of the prime optical center in GaN:Eu3+. *Physical Review B*, **2010**, 81,	3.3	61
260	The influence of interface roughness on the magnetic properties of exchange biased CoO/Fe thin films. *Journal of Applied Physics*, **2010**, 107, 113907	2.5	25
259	In situ X-ray diffraction study of thin film Ir/Si solid state reactions. *Microelectronic Engineering*, **2010**, 87, 258-262	2.5	7
258	In situ study of the formation of silicide phases in amorphous Co–Si mixed layers. *Microelectronic Engineering*, **2010**, 87, 282-285	2.5	3
257	Pd as a promoter to reduce Co cluster films at room temperature. *International Journal of Hydrogen Energy*, **2010**, 35, 2262-2267	6.7	10
256	Artificial neural networks for instantaneous analysis of real-time Rutherford backscattering spectra. *Nuclear Instruments & Methods in Physics Research B*, **2010**, 268, 1676-1681	1.2	21
255	Artificial neural networks applied to the analysis of synchrotron nuclear resonant scattering data. *Journal of Synchrotron Radiation*, **2010**, 17, 86-92	2.4	6
254	Lattice Location of RE Impurities in IIINitrides. *Topics in Applied Physics*, **2010**, 55-98	0.5	3
253	Probing the dynamical properties of the metastable bcc FexCo1−x phase. *Physical Review B*, **2009**, 79,	3.3	4
252	Optical and structural properties of Eu-implanted InxAl1−xN. *Journal of Applied Physics*, **2009**, 106, 083508	2.5	2
251	Lattice location study of implanted In in Ge. *Journal of Applied Physics*, **2009**, 105, 083522	2.5	24
250	Changing the three-dimensional magnetization exchange coupling of mixed Fe and V nanoclusters with hydrogen. *Journal of Applied Physics*, **2009**, 105, 114907	2.5	6

249	On the thermal expansion coefficient of CoSi2and NiSi2. *Journal Physics D: Applied Physics*, **2009**, 42, 235402	3	19
248	Transition metal impurities on the bond-centered site in germanium. *Physical Review Letters*, **2009**, 102, 065502	7.4	27
247	Investigations of the Surface Chemical Composition and Atomic Structure of ex-situ Sulfur Passivated Ge(100). *ECS Transactions*, **2009**, 25, 421-432	1	4
246	Interplay between structural and magnetic properties of L10-FePt(001) thin films directly grown on MgO(001). *Journal of Applied Physics*, **2009**, 105, 073913	2.5	27
245	Diffusion, nucleation and reaction in a three-component system: Fe on Si(111)-□□□u. *New Journal of Physics*, **2009**, 11, 093019	2.9	4
244	Implantation-induced damage in Ge: strain and disorder profiles during defect accumulation and recovery. *Journal Physics D: Applied Physics*, **2009**, 42, 165404	3	29
243	The Influence of an Adsorbate Layer on Adatom Diffusion and Island Nucleation: Fe on Si(111)-□□-Au. *Nanoscale Research Letters*, **2009**, 4, 1447-1451	5	4
242	Effect of fluence on the lattice site of implanted Er and implantation induced strain in GaN. *Nuclear Instruments & Methods in Physics Research B*, **2009**, 267, 1340-1344	1.2	
241	Considerations about multiple and plural scattering in heavy-ion low-energy ERDA. *Nuclear Instruments & Methods in Physics Research B*, **2009**, 267, 1936-1941	1.2	2
240	Electrical characterization of rare-earth implanted GaN. *Physica B: Condensed Matter*, **2009**, 404, 4411-4414	1.8	12
239	Optimizing the growth of CoSi2 film with oxide-mediated CoSi2 template by silicon cap layer. *Journal of Crystal Growth*, **2009**, 311, 4007-4010	1.6	
238	Size-dependent optical properties of colloidal PbS quantum dots. *ACS Nano*, **2009**, 3, 3023-30	16.7	847
237	M□ssbauer studies of complex materials: Energy versus time domain. *Applied Physics Letters*, **2009**, 94, 224104	3.4	5
236	Iron silicide nanostructure formation on Au induced superstructures on Si(111). *Nanotechnology*, **2009**, 20, 075607	3.4	1
235	Pt redistribution during Ni(Pt) silicide formation. *Applied Physics Letters*, **2008**, 93, 261912	3.4	43
234	Simultaneous real-time x-ray diffraction spectroscopy, Rutherford backscattering spectrometry, and sheet resistance measurements to study thin film growth kinetics by Kissinger plots. *Journal of Applied Physics*, **2008**, 104, 103538	2.5	7
233	Nucleation and diffusion during growth of ternary Co1□NixSi2 thin films studied by complementary techniques in real time. *Journal of Applied Physics*, **2008**, 104, 093533	2.5	13
232	The role of lattice mismatch and kinetics in texture development: Co1□NixSi2 thin films on Si(100). *Journal of Applied Physics*, **2008**, 103, 063506	2.5	18

231	Optical energies of AlInN epilayers. *Journal of Applied Physics*, **2008**, 103, 073510	2.5	56
230	Experimental evidence of tetrahedral interstitial and bond-centered Er in Ge. *Applied Physics Letters*, **2008**, 93, 141907	3.4	11
229	High-temperature AlN interlayer for crack-free AlGaN growth on GaN. *Journal of Applied Physics*, **2008**, 104, 043516	2.5	8
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